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Bulk defect investigations for proton irradiated sensors

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For irradiation experiments, protons with energies ranging from 23 MeV to 23 GeV are often used instead of a mixture of charged hadrons, their radiation induced damage to the silicon being rather similar. However, in oxygen rich silicon, NIEL violation con- cerning the full depletion voltage has been observed. In this presentation results from investigations on bulk defects in silicon pad-sensorswill be presented after irradiations with 23 MeV, 800 MeV and 23 GeV protons.

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